



PATENT
Attorney Docket No.: SAM-0266

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Ku, et al.
Serial No.: 09/992,980
Filing Date: November 6, 2001
Title: METHOD OF FORMING A METAL GATE ELECTRODE

Examiner: Lee, C.
Group Art Unit: 2825

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Date

Amy Green
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Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

AMENDMENT A

Sir:

This is in response to the Office Action mailed on December 26, 2002. The applicants request a two-month extension of the time allowed for response. A petition for the extension and the extension fee are enclosed.

Please amend the application as follows:

In the Specification

Please replace the paragraph at page 3 line 12 through page 4 line 4 with the following rewritten paragraph.

-- However, the selective oxidation process described above has a narrow process margin, and it is difficult to adjust the partial pressures of the hydrogen gas and H₂O to only oxidize the silicon. Accordingly, as shown in Fig. 2A, a small amount of the tungsten is oxidized, so that tungsten oxide 12c is formed on side walls of the tungsten layer 16. As shown in Fig. 2B, the

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